

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

TMD5872-2

PRELIMINARY

FEATURES

- High Power $P_{1dB}=34\text{dBm(TYP.)}$
- High Power Added Efficiency $\eta_{add}=21\%(TYP.)$
- High Gain $G_{1dB}=28\text{dB(TYP.)}$
- Broadband Operation $f=5.8\text{-}7.2\text{GHz.}$

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

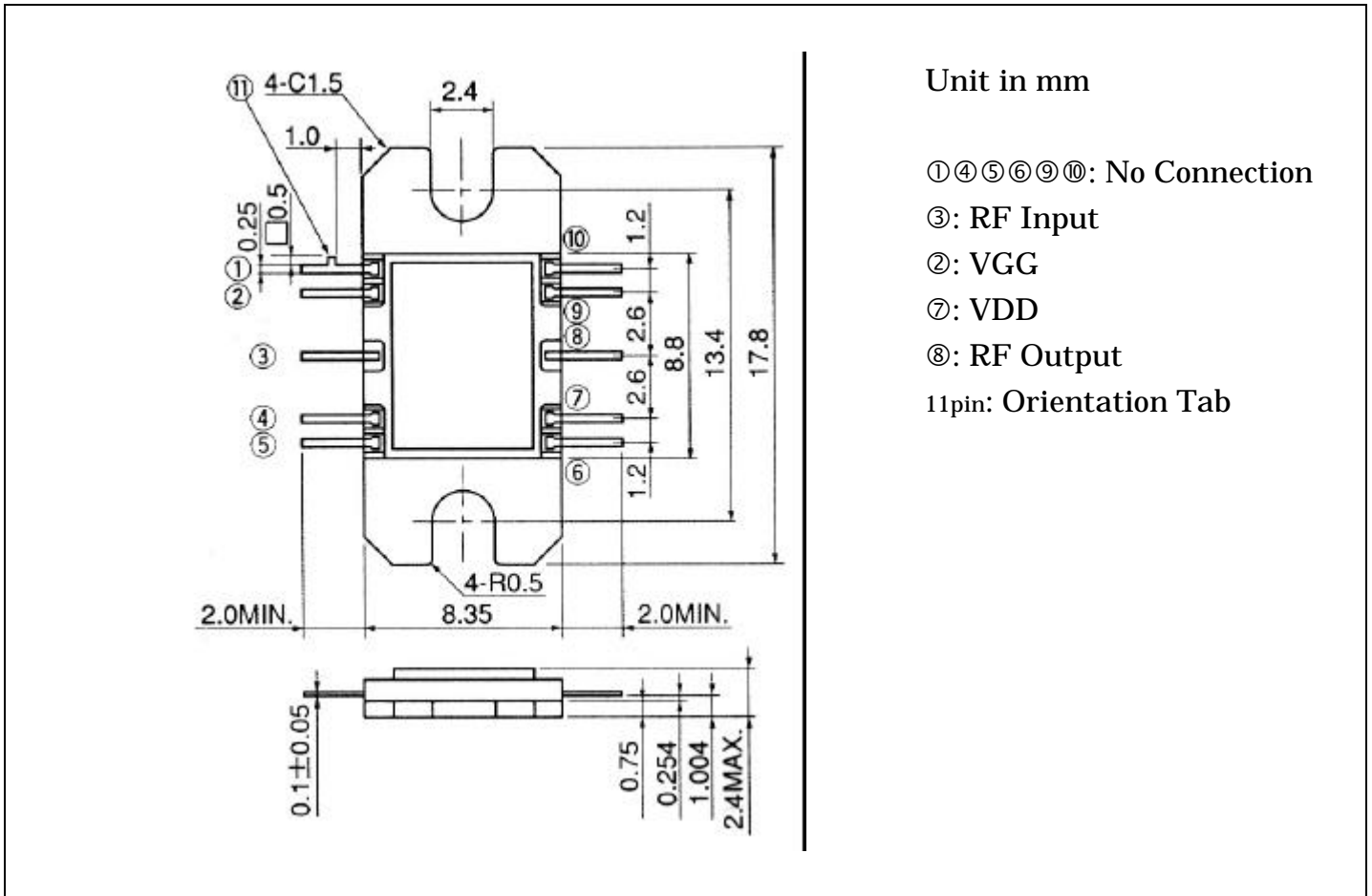
CHARACTERISTICS	SYMBOL	UNIT	RATINGS
DRAIN SUPPLY VOLTAGE	VDD	V	15
GATE SUPPLY VOLTAGE	VGG	V	-10
INPUT POWER	Pin	dBm	10
FLANGE TEMPERATURE	Tf	°C	-30 - +80
STORAGE TEMPERATURE	Tstg	°C	-65 - +175

RF PERFORMANCE SPECIFICATIONS ($T_a=25^\circ\text{C}$)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.	
Operating Frequency	f	VDD=10V VGG=-5V	GHz	5.8	-	7.2	
Output Power at 1dB Gain Compression Point	P1dB		dBm	32	34	-	
Power Gain at 1dB Gain Compression Point	G1dB		dB	25	28	-	
Gain Flatness	G		dB	-	-	± 2.0	
Drain Current	IDD		A	-	1.2	1.6	
Power Added Efficiency	η_{add}		%	-	21	-	
VSWRin (small signal)	VSWRin		-	-	-	2.0:1	3.0:1

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Package Outline



Recommended Bias Configuration

